



MEMC 98-1451/2554.1  
PATENT

#5/B  
SA  
6/10/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster et al.

Art Unit 1775

Serial No. 10/073,506

Filed February 11, 2002

Confirmation No. 6190

For THERMAL ANNEALING PROCESS FOR PRODUCING LOW DEFECT  
DENSITY SINGLE CRYSTAL SILICON

Examiner Matthew A. Anderson

May 29, 2003

RECEIVED

JUN 09 2003

AMENDMENT B

TC 1700

TO THE COMMISSIONER FOR PATENTS,

SIR:

Please enter the following amendment, which is submitted in accordance with the proposed format revisions to 37 CFR 1.121, in response to the Office Action dated November 29, 2002:

Adjustment date 06/03/2003 WARDER1 191345 10073506  
06/02/2003 WARDER1 00000093 191345 10073506  
03-FE1202 36.00 CR 684.00 OP

06/02/2003 WARDER1 00000093 191345 10073506  
- 01 FC:1253 930.00 OP

06/02/2003 WARDER1 00000093 191345 10073506  
03 FC:1282 36.00 CH 684.00 OP  
06/03/2003 WARDER1 00000010 10073506  
01 FC:1202 684.00 OP